2SD1922

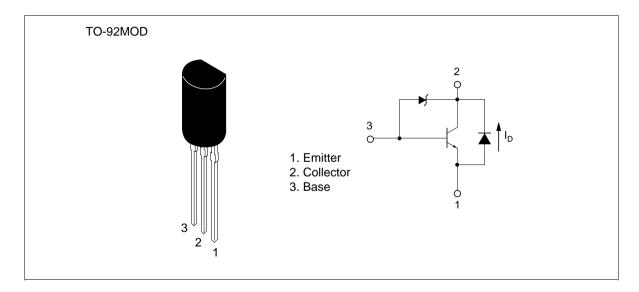
Silicon NPN Epitaxial

HITACHI

Application

Low frequency power amplifier

Outline





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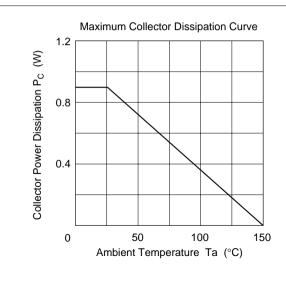
Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

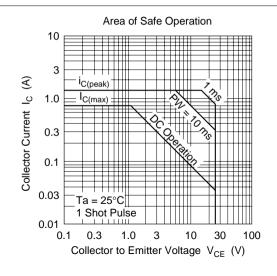
| Item | Symbol | Ratings | Unit |
|------------------------------|----------------------|-------------|------|
| Collector to base voltage | V_{CBO} | 25 | V |
| Collector to emitter voltage | V _{CEO} | 25 | V |
| Emitter to base voltage | V_{EBO} | 6 | V |
| Collector current | I _c | 0.8 | A |
| Collector peak current | ic _(peak) | 1.5 | A |
| E to C diode forward current | I _D | 0.8 | A |
| Collector power dissipation | P _c | 0.9 | W |
| Junction temperature | Tj | 150 | °C |
| Storage temperature | Tstg | -55 to +150 | °C |

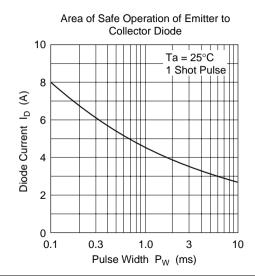
Electrical Characteristics ($Ta = 25^{\circ}C$)

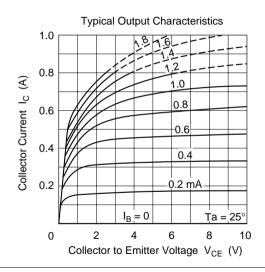
| Item | Symbol | Min | Тур | Max | Unit | Test conditions |
|---|-----------------------|-----|-----|------|------|---|
| Collector to base breakdown voltage | $V_{(BR)CBO}$ | 25 | _ | _ | V | $I_{C} = 10 \ \mu\text{A}, \ I_{E} = 0$ |
| Collector to emitter breakdown voltage | $V_{(BR)CEO}$ | 25 | _ | 35 | V | I_{C} = 1 mA, R_{BE} = ∞ |
| Collector to emitter sustaining voltage | $V_{\text{CEO(sus)}}$ | 25 | _ | 35 | V | $I_{C} = 0.8 \text{ A}, R_{BE} = \infty,$ L = 20 mH |
| Emitter to base breakdown voltage | $V_{(BR)EBO}$ | 6 | _ | _ | V | $I_{E} = 10 \ \mu A, \ I_{C} = 0$ |
| Collector cutoff current | I _{CBO} | _ | _ | 0.2 | μΑ | V _{CB} = 20 V, I _E = 0 |
| | I _{CEO} | _ | _ | 0.5 | μΑ | $V_{CE} = 20 \text{ V}, R_{BE} = \infty$ |
| Emitter cutoff current | I _{EBO} | _ | _ | 0.2 | μΑ | $V_{EB} = 5 \text{ V}, I_{C} = 0$ |
| DC current transfer ratio | h _{FE} | 250 | _ | 1200 | | $V_{CE} = 2 \text{ V}, I_{C} = 0.1 \text{ A}^{*1}$ |
| Collector to emitter saturation voltage | $V_{\text{CE(sat)}}$ | _ | _ | 0.3 | V | $I_{\rm C} = 0.8 \text{ A}, I_{\rm B} = 80 \text{ mA}^{*1}$ |
| E to C diode forward voltage | V _D | _ | _ | 1.1 | V | $I_D = 0.8 \text{ A}^{*1}$ |

Note: 1. Pulse test

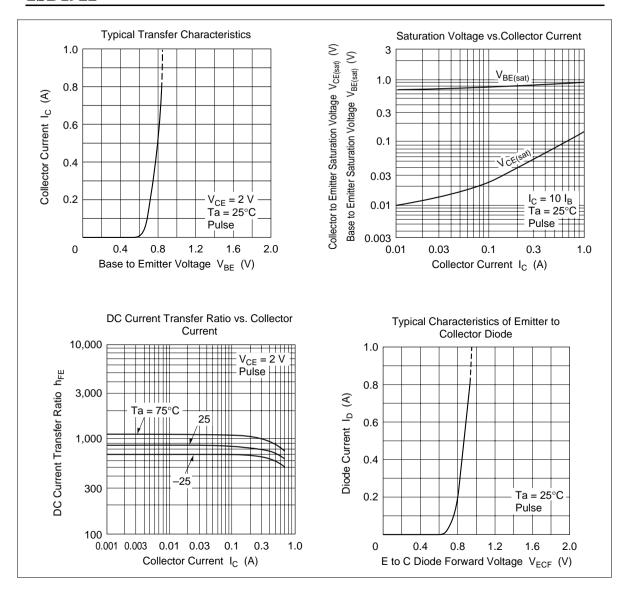


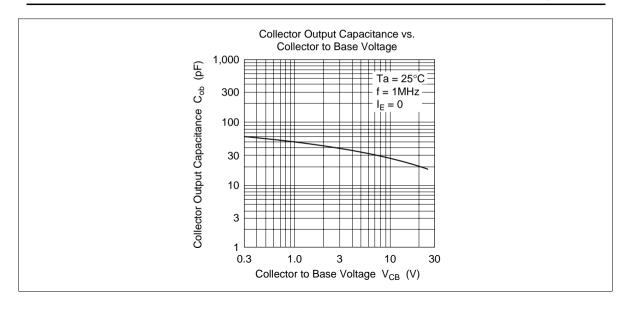




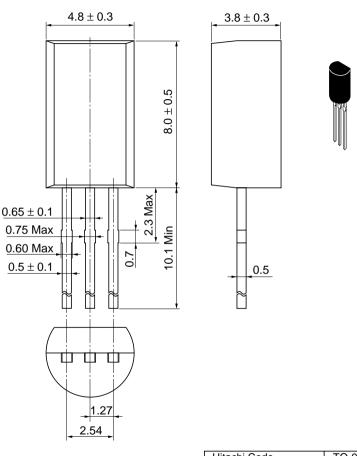


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Unit: mm



Hitachi Code TO-92 Mod

JEDEC —

EIAJ Conforms

Weight (reference value) 0.35 g

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